IN THE CLAIMS:

1. (Currently Amended) A method for drying circuit substrates [[(13)]], in particular semiconductor substrates, the method comprising:

providing a receiving system, said receiving system receiving at least one circuit substrate;

flushing ~~in which~~ a circuit surface ~~(29,30)~~ of the at least one circuit substrate ~~is flushed~~ using a flushing liquid [[(10)]] in a flushing step;

providing a thermal radiator unit; and

drying the circuit surface ~~is dried~~ in a subsequent drying step, the at least one circuit substrate being moved in the flushing step in the direction of its planar extension transversely and in relation to a liquid level [[(28)]] of the flushing liquid in such a way that a liquid meniscus ~~(31,32)~~ forms at a transition area [[(35)]] between the circuit surface and the liquid level, which changes because of the relative movement, and thermal radiation [[(36)]] is applied to the transition area wetted by the liquid meniscus in the drying step via said thermal radiator unit, said thermal radiator unit being arranged at a position above said receiving system and the circuit substrate.

2. (Currently Amended) The method according to [[Claim]] claim 1, ~~characterized in that~~ wherein said thermal radiator unit comprises ~~radiation (36) is applied using~~ an infrared radiator.

3. (Currently Amended) The method according to [[Claim]] claim 1, ~~characterized in that~~ wherein to perform the relative movement between the liquid level [[(28)]] and the circuit substrate [[(13)]], the circuit substrate is situated in the flushing liquid [[(10)]] received by a bath container [[(11)]] and the liquid level is lowered.

4. (Currently Amended) The method according to [[Claim]] claim 1, ~~characterized in that~~ wherein thermal radiation [[(36)]] is applied transversely to the liquid level [[(28)]].

5. (Canceled)

6. (Currently Amended) The method according to [[Claim]] claim 1, ~~characterized in that~~ wherein multiple flushing steps are performed through repeated flooding of the bath container before performing the drying step in [[the]] a bath container [[(11)]].

7. (Currently Amended) A device for performing a method for drying circuit substrates [[(13)]], in particular semiconductor substrates, ~~according to Claim 1~~, the device comprising: ~~having~~

a bath container [[(11)]], which is provided with an inflow unit [[(16)]] and an outflow unit [[(17)]] and is closable using a cover unit; ~~(20), and~~

a receiving system [[(12)]], which is situated in the bath container, for receiving at least one circuit substrate in such a way that the circuit substrate extends in a plane in the direction

of a container floor of said bath container; ~~(14),~~ and ~~having~~

a thermal radiator unit [[(22)]] situated above the receiving system so as to allow simultaneous application to multiple circuit substrates arranged in said receiving system.

8. (Currently Amended) The device according to [[Claim]] claim 7, ~~characterized in that~~ wherein the thermal radiator unit [[(22)]] is provided with infrared radiators.

9. (Currently Amended) The device according to [[Claim]] claim 7, ~~characterized in that~~ wherein the thermal radiator unit [[(22)]] is situated on the cover unit [[(20)]].

10. (Currently Amended) The device according to [[Claim]] claim 7, ~~characterized in that~~ wherein the thermal radiator unit [[(22)]] is situated above a transparent plate [[(25)]] for separation from a container interior.

11. (Currently Amended) The device according to [[Claim]] claim 7, ~~characterized in that~~ wherein the bath container [[(11)]] is provided with a ventilation unit in [[the]] an area of the cover unit ~~(20) with a ventilation unit (27)~~.

12. (Currently Amended) The device according to [[Claim]] claim 11, ~~characterized in that~~ wherein the ventilation unit [[(27)]] is situated on the cover unit [[(20)]].

13. (New) A method in accordance with claim 1, further comprising:

providing a bath container, said receiving system being arranged in said bath container, said flushing liquid being provided in said bath container, wherein said drying step includes decreasing a level of said flushing liquid in said bath container and applying said thermal radiation to said transition area as said level of said flushing liquid is decreased.

14. (New) A method in accordance with claim 1, further comprising:

providing a bath container, said receiving system being arranged in said bath container, said flushing liquid being provided in said bath container, wherein said drying step includes decreasing an amount of said flushing liquid in said bath container such that at least a portion of said at least one circuit substrate is located at a spaced location from said flushing liquid and at least another portion of said at least one circuit substrate is in contact with said flushing liquid.

15. (New) A device in accordance with claim 7, wherein a fluid is provided in said bath container, said fluid being at a first fluid level with said outflow unit in a closed state, said fluid being at a second fluid level with said outflow unit in an open state, said first fluid level being greater than said second fluid level, one or more of said circuit substrates being located at a position below said first fluid level with said outflow unit in said closed state, said one more of said circuit substrates having at least one portion located at a spaced location from said flushing liquid and at least another portion in contact with said flushing liquid with said

outflow unit in said open state, said thermal radiation unit applying thermal radiation to said one more of said circuit substrates with said outflow unit in the open state.

16. (New) A method, comprising:

providing at least one circuit substrate in a receiving system, said at least one circuit substrate comprising a circuit surface;

providing a fluid holding structure, said receiving system with said at least one substrate being arranged in said fluid holding structure;

providing a fluid;

delivering said fluid to said fluid holding structure such that said fluid is provided at or above a surface of said receiving system;

providing a thermal radiator unit, said thermal radiator unit being arranged at a position above said receiving system and said at least one circuit substrate;

decreasing an amount of said fluid in said fluid holding structure after delivering said fluid to said fluid holding structure;

drying said circuit surface with said thermal radiator unit after or during said step of decreasing said amount of said fluid.

17. (New) A method in accordance with claim 16, wherein a liquid meniscus forms at a transition area between the circuit surface and a fluid level of said fluid after decreasing said amount of fluid in said fluid holding structure, said at least one circuit substrate being

moved in a direction of a planar extension thereof, said direction of said planar extension being transverse to said fluid level, wherein thermal radiation is applied to the transition area wetted by the liquid meniscus in the drying step via said thermal radiator unit.

18. (New) A method in accordance with claim 16, wherein an amount of said fluid in said bath container is decreased such that at least a portion of said at least one circuit substrate is located at a position above a level of said fluid and at least another portion of said at least one circuit substrate is in contact with said fluid.

19. (New) A method in accordance with claim 16, wherein thermal radiation is applied to said transition area via said thermal radiation unit as said amount of said fluid is decreased.

20. (New) A method in accordance with claim 16, wherein said fluid holding structure is connected to an inflow unit and an outflow unit, said fluid being at a first fluid level with said outflow unit in a closed state, said fluid being at a second fluid level with said outflow unit in an open state, said first fluid level being greater than said second fluid level, said at least one circuit substrate being located at a position below said first fluid level with said outflow unit in said closed state, said at least one circuit substrate having at least one portion located at a spaced location from said flushing liquid and at least another portion in contact with said flushing liquid with said outflow unit in said open state, said thermal radiation unit applying thermal radiation to said at least one circuit substrate with said outflow unit in the open state.